

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

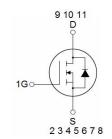
- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

General Features

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP018N85LL	NCEP018N85LL	TOLL	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	VDS	85	V	
Gate-Source Voltage	V _G s	±20	V	
Drain Current-Continuous	I _D	320	Α	
Drain Current-Continuous(T _C =100℃)	I _D ((T _C =100℃)	245	А	
Pulsed Drain Current	I _{DM}	1280	А	
Maximum Power Dissipation	P _D	380	W	
Derating factor		2.5	W/℃	
Single pulse avalanche energy (Note 1)	E _{AS}	2880	mJ	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$	

Thermal Characteristic

Thermal Resistance, Junction-to-Case Reuc	0.4	°C/W
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Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics	·					•
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =160A	-	1.3	1.8	mΩ
Gate resistance	R _G	F=1.0MHz	-	3.0	-	Ω
Forward Transconductance	g FS	V _{DS} =5V,I _D =160A		200	-	S
Dynamic Characteristics	·					•
Input Capacitance	C _{lss}	\/ -40\/\/ -0\/	-	14500	-	PF
Output Capacitance	Coss	V_{DS} =40V, V_{GS} =0V, F=1.0MHz	-	2050	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1.0lvinz	-	105	-	PF
Switching Characteristics (Note 2)						•
Turn-on Delay Time	t _{d(on)}		-	34	-	nS
Turn-on Rise Time	t _r	V_{DD} =40 V , I_{D} =160 A	-	27	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =10 V , R_{G} =1.6 Ω	-	78	-	nS
Turn-Off Fall Time	t _f		-	30	-	nS
Total Gate Charge	Qg	\/ -40\/ L -400A	-	240	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =40V,I _D =160A,	-	61		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V		72		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =160A	-		1.2	V
Diode Forward Current	Is		-	-	320	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 160A	-	101	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	280	-	nC
			-	-		

Notes:

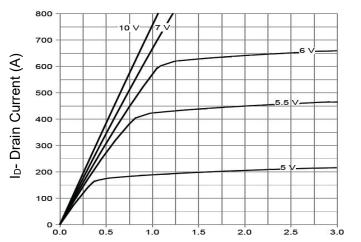
^{1.} EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=40V,VG=10V,L=0.5mH,Rg=25 Ω

^{2.} Guaranteed by design, not subject to production

^{3.} These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

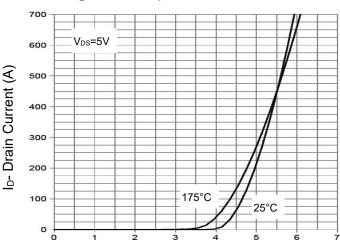


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

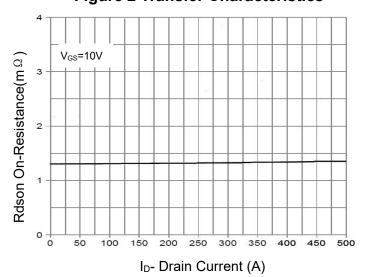
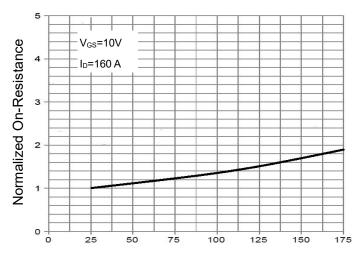


Figure 3 Rdson- Drain Current



T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature

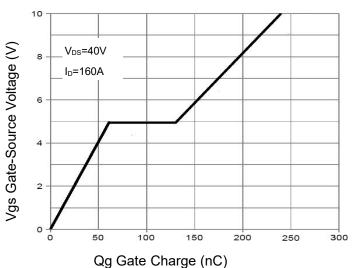
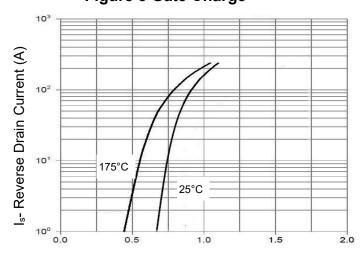


Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



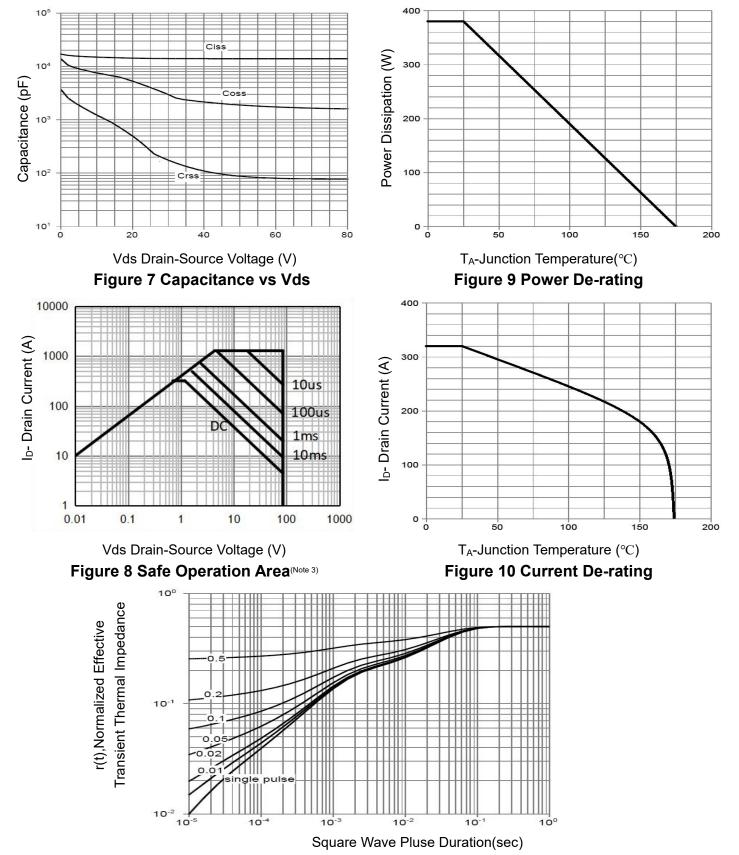
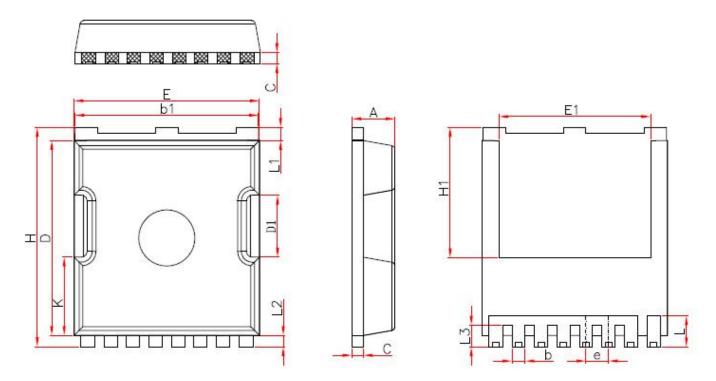


Figure 11 Normalized Maximum Transient Thermal Impedance



TOLL Package Information



Symbol	Millimeters			
VIII.	Min.	Nom.	Max.	
A	2.20	2.30	2.40	
b	0.65	0.75	0.85	
b1	9.70	9.80	9.90	
С	0.50	0.60	0.70	
D	10.30	10.40	10.50	
D1	3.15	3.3	3.45	
Е	9.70	9.90	10.10	
E1	8.00	8.10	8.20	
е	1.10	1.20	1.30	
Н	11.6	11.7	11.8	
H1	6.85	6.95	7.05	
K	4.08	4.18	4.28	
L	1.60	1.65	2.10	
L1	0.60	0.70	0.80	
L2	0.50	0.60	0.70	
L3	1.05	1.20	1.30	

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